

KSK117**SILICON N-CHANNEL JUNCTION FET**

T-29-25

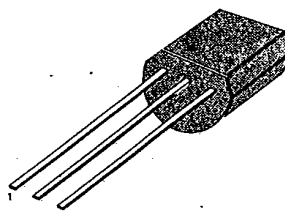
LOW FREQUENCY LOW NOISE AMP.High $|Y_{fs}|$: 15mS (TYP)High Input Impedance: $I_{gss} = -1nA$

Low Noise, NF = 1dB (TYP)

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Gate-Drain Voltage	V_{gds}	-50	V
Gate Current	I_g	10	mA
Collector Dissipation	P_C	300	mW
Junction Temperature	T_J	125	$^\circ C$
Storage Temperature	T_{stg}	-55~125	$^\circ C$

TO-92



1. Drain 2. Source 3. Gate

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Gate-Drain Breakdown Voltage	BV_{gds}	$V_{DS}=0, I_g = -100\mu A$	-50			V
Gate Leak Current	I_{gss}	$V_{gs} = -30V, V_{DS}=0$			-1	nA
Drain Leak Current	I_{DSS}	$V_{DS}=10V, V_{GS}=0$	0.6		14	mA
Gate-Source Voltage	$V_{gs(off)}$	$V_{DS}=10V, I_D=0.1\mu A$	-0.2		-1.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=10V, V_{gs}=0, f=1KHz$	4.0	15		mS
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{gs}=0, f=1MHz$		13		pF
Feedback Capacitance	C_{rss}	$V_{gs}=10V, I_D=0$ $f=1MHz$		3		pF
Noise Figure	NF1	$V_{DS}=10V, R_g=1k\Omega$ $I_D=0.5mA, f=10Hz$		5	10	dB
	NF2	$V_{DS}=10V, R_g=1k\Omega$ $I_D=0.5mA, f=1KHz$		1	2	dB

 I_{DSS} CLASSIFICATION

Classification	Y	G	L
$I_{DSS}(mA)$	1.2-3.0	2.6-6.5	6.0-14

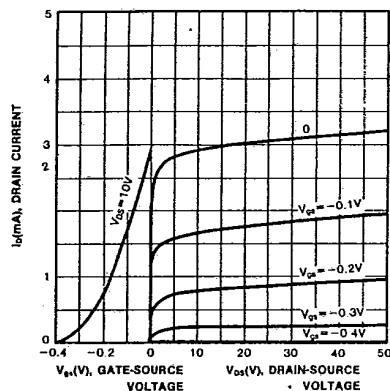
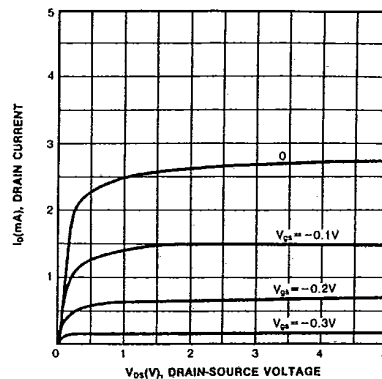
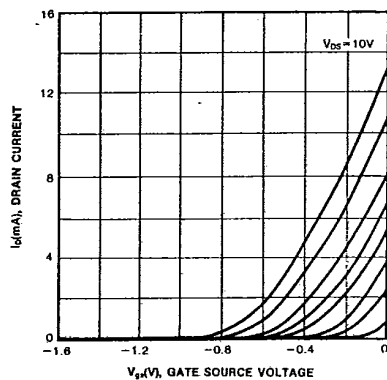
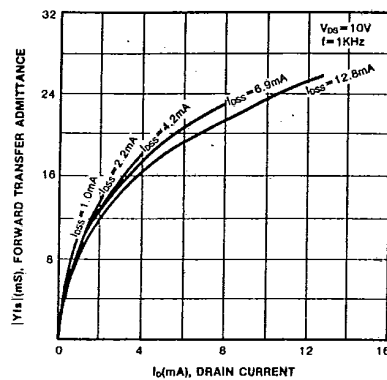
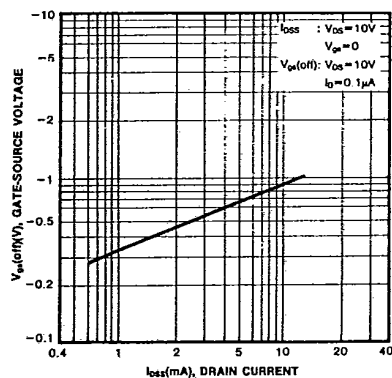
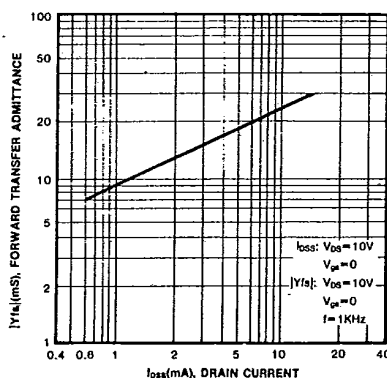


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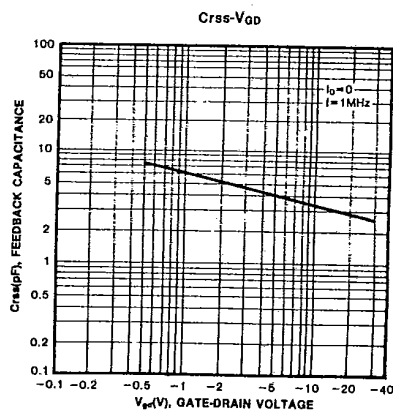
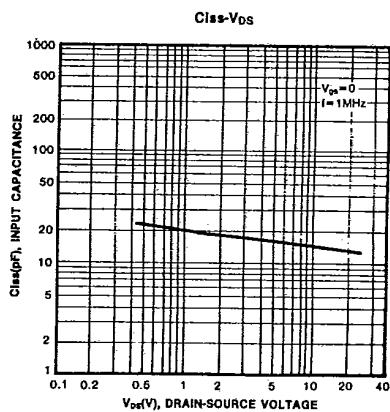
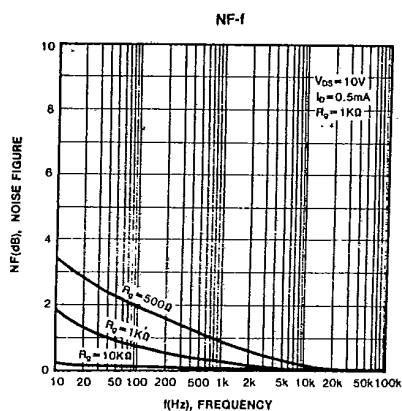
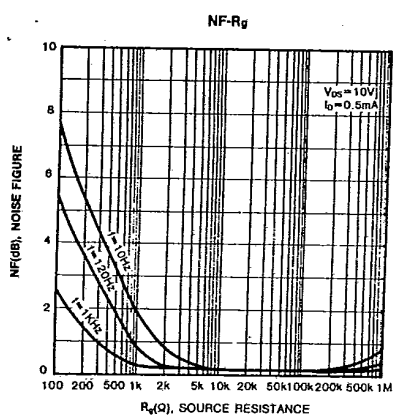
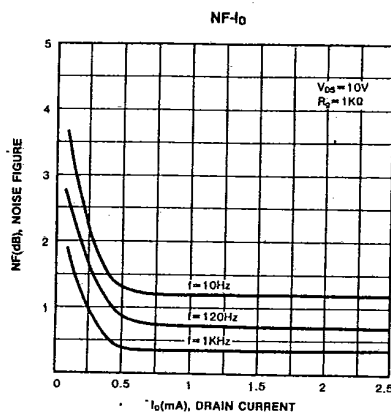
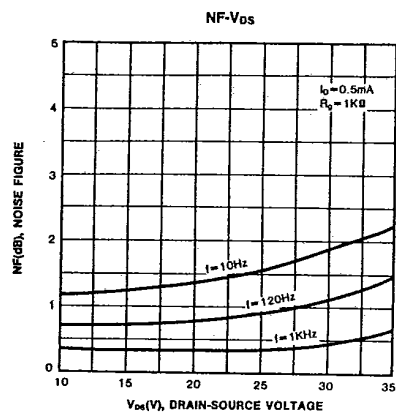
STATIC CHARACTERISTIC

 I_D - V_{DS}  I_D - V_{GS}  $|Y_{fs}|$ - I_D  $V_{GS(off)}$ -loss $|Y_{fs}|$ -loss

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